

FIG. 1A

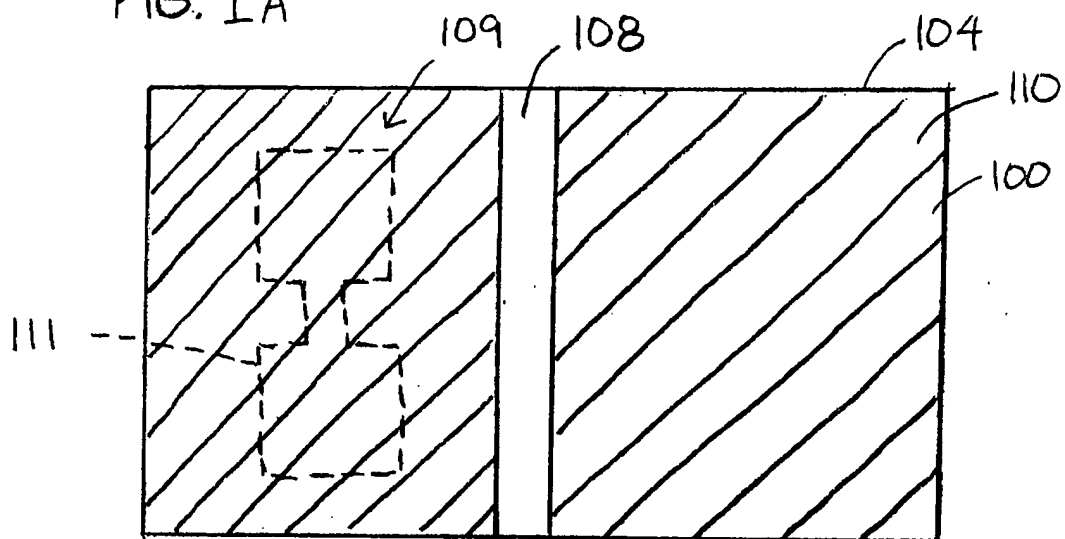


FIG. 1B

FIG. 15 is a cross-sectional view of a device. It features a central channel (118) flanked by side structures (112, 114). The top surface is labeled 100, and the bottom surface is labeled 102. The side structures are labeled 110 and 116. The channel walls are labeled 104 and 106. The channel floor is labeled 108. The top surface is also labeled 120. The side structures are also labeled 120.

FIG. 1C is a schematic diagram of a device structure. It shows a rectangular block with a central region 108, a left hatched region 120, and a right hatched region 104. A dashed line 109 defines a stepped profile within the central region. Labels 114, 111, 116, 110, 118, and 120 point to various boundaries and features.

FIG. 1D

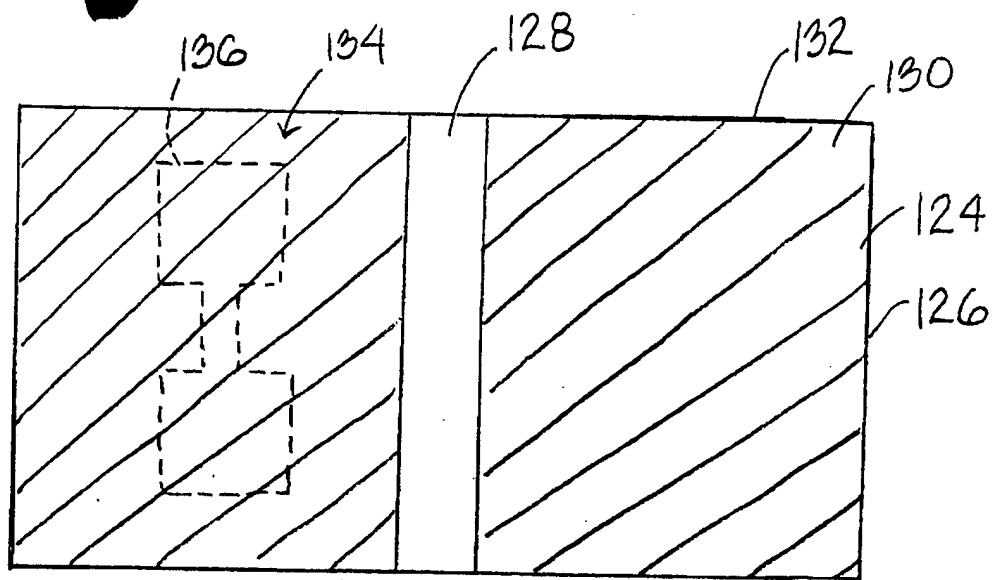


FIG. 2A

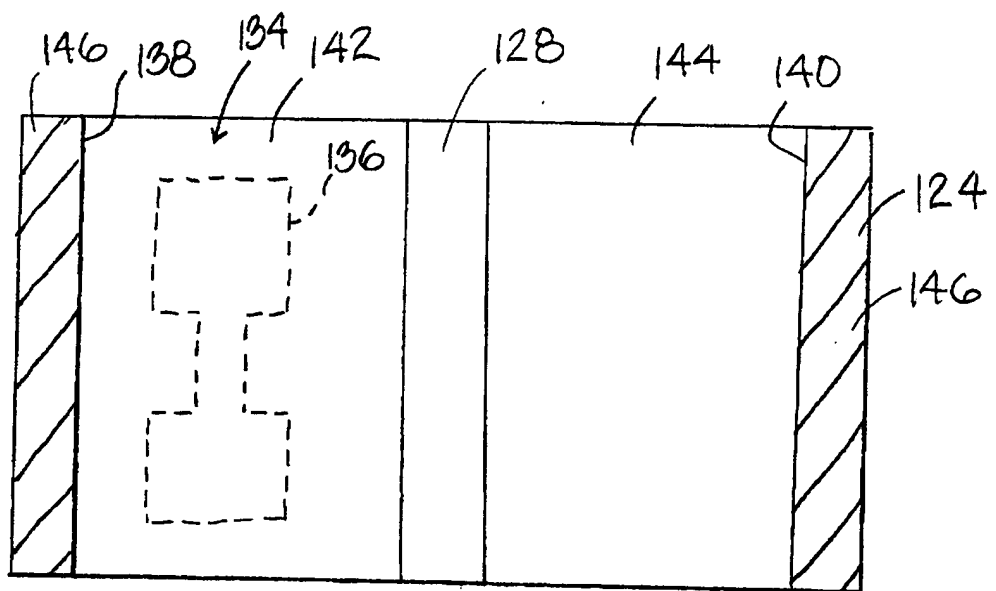


FIG. 2B

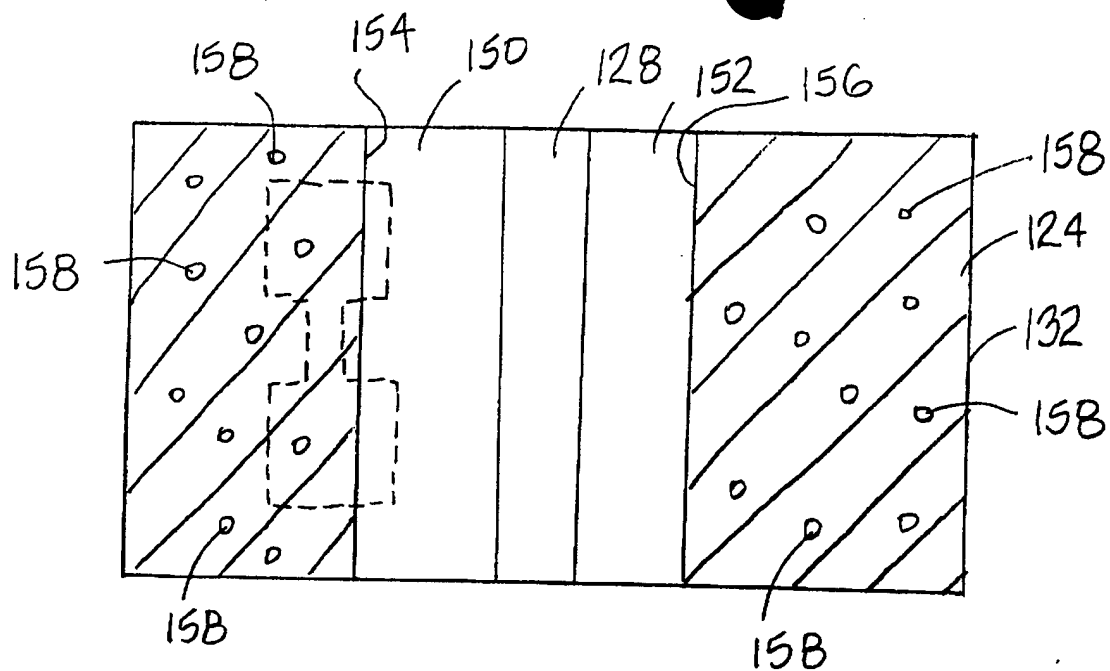


FIG. 2C

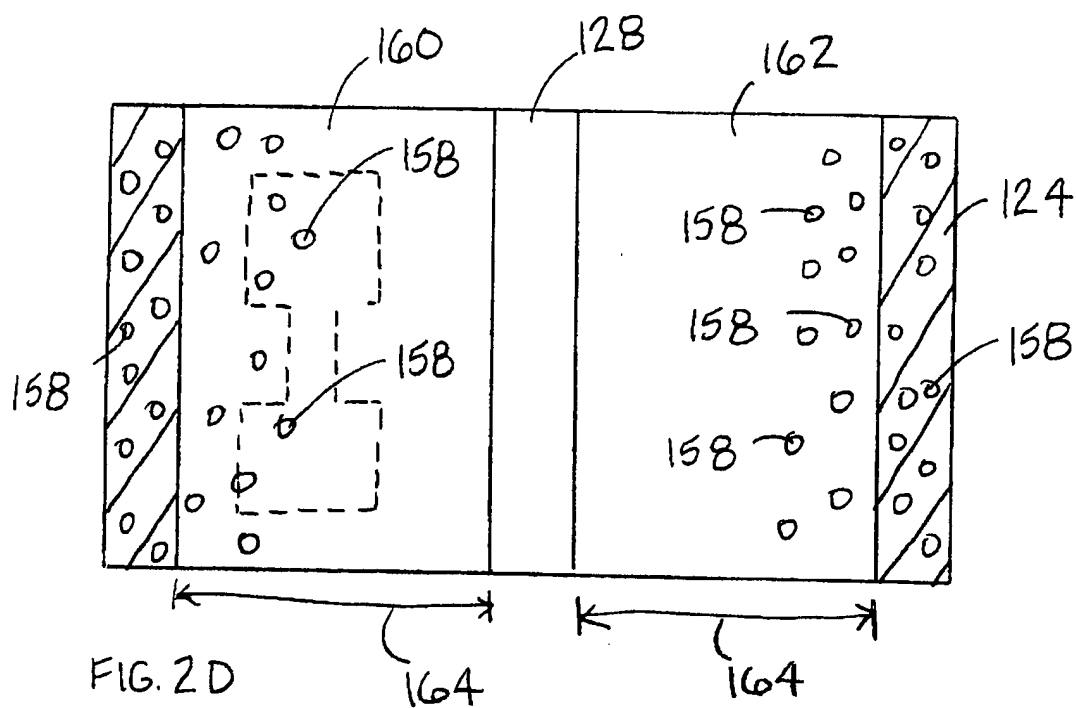


FIG. 2D

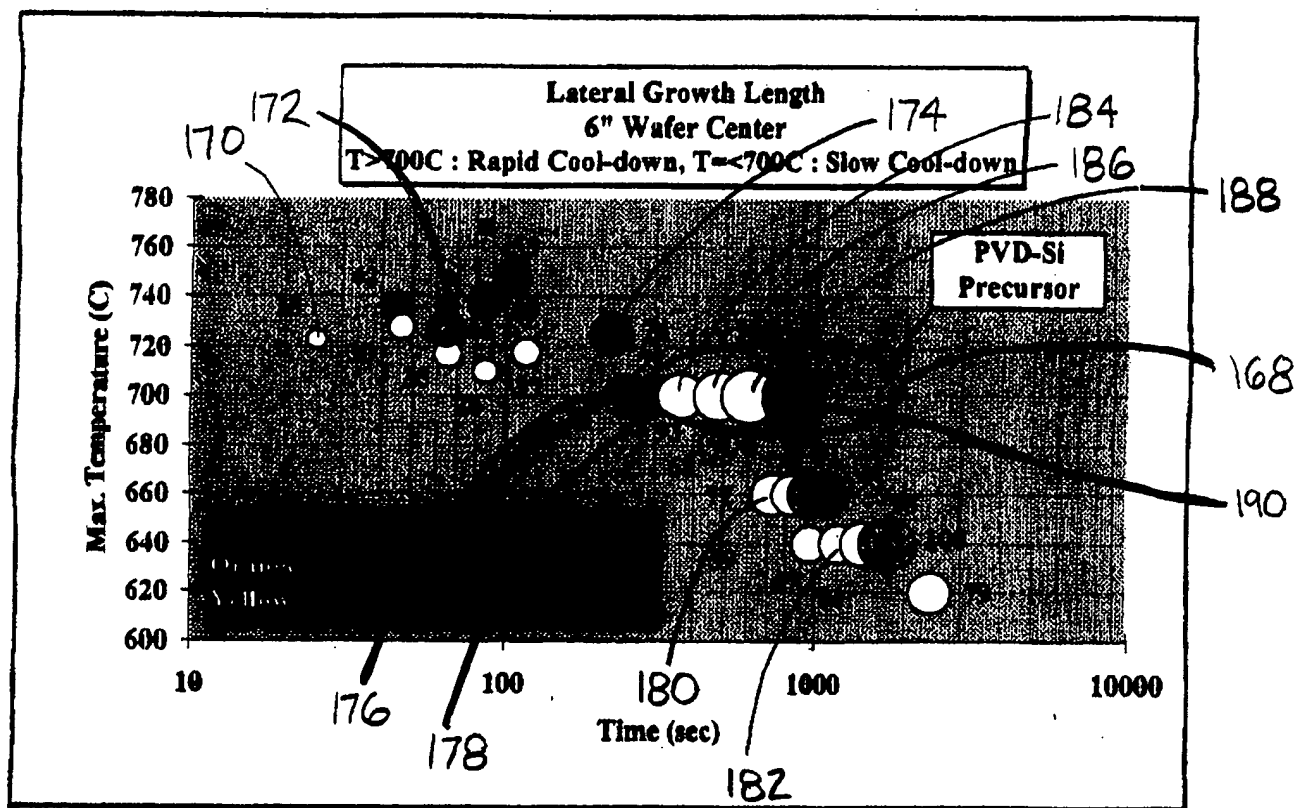


FIG. 3

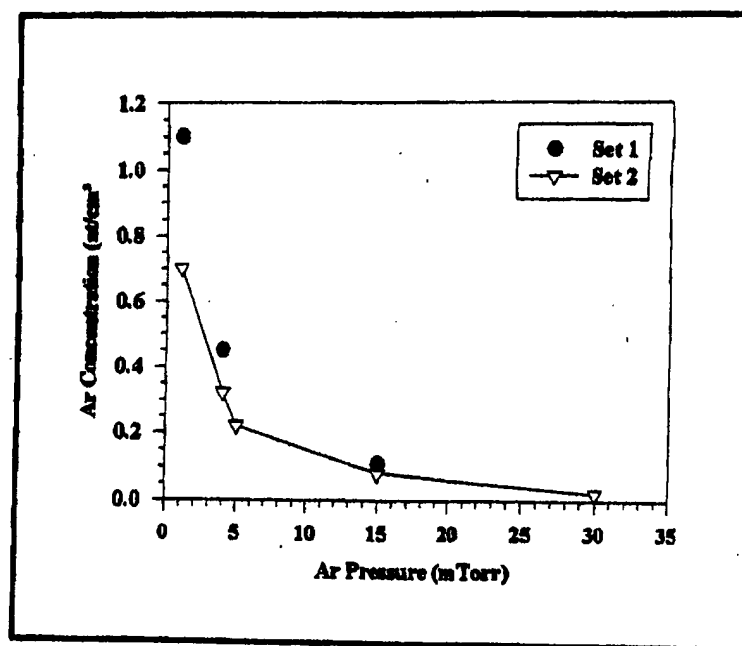


FIG. 4

Power (kW)	Pressure (mTorr)	Sputtering Gas	Ar content (at/cm ³)
8	14-16	Pure He	$<2 \times 10^{18}$
		He/(3.8%)Ar	$2-5 \times 10^{18}$
		He/(10%)Ar	$4-7 \times 10^{18}$
		Pure Ar	6×10^{19}
8	5-6	Pure Ar	2×10^{20}

FIG. 5

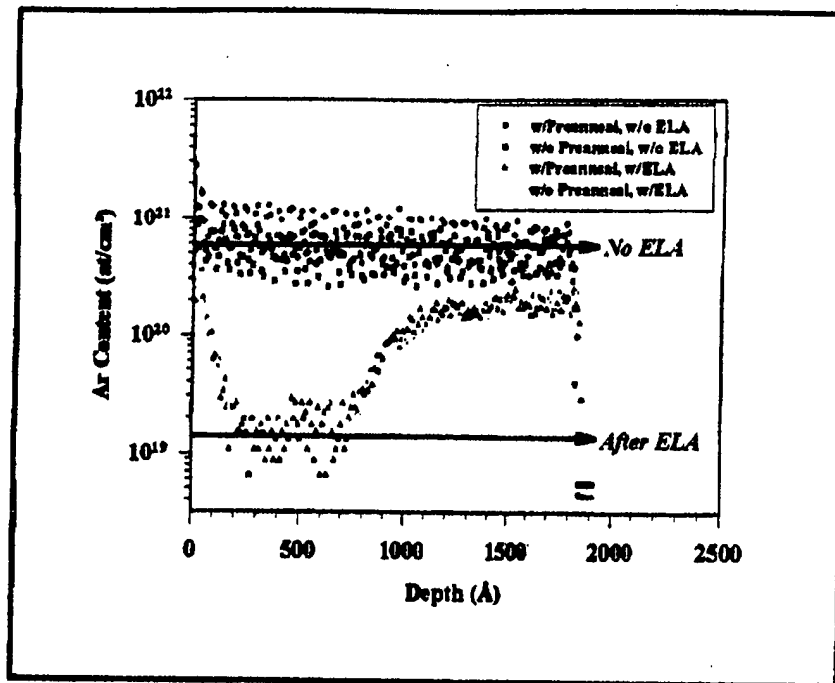


FIG. 6

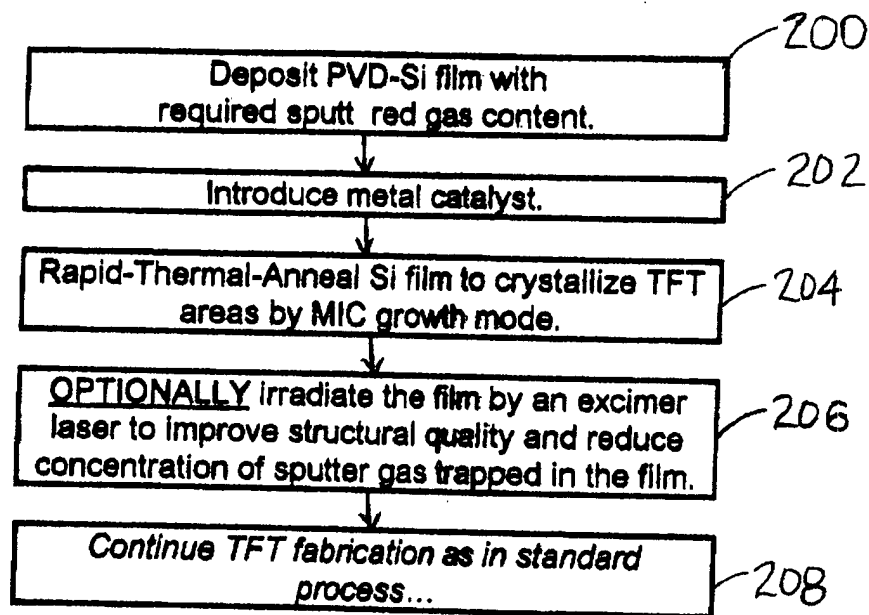


FIG. 7